Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- (Original) Inorganic, quasi-amorphous oxide compound of a metal, mixture of metals or semi conducting element, said compound having pyrolelectric properties.
- 2. (Original) The compound of claim 1 having the formula $(A_xB_{1-x})_pO_n$, wherein A and B are independently selected from transitions metals, elements of Group IVA of the periodic table, alkali metals, alkali earth metals and rare earth metals; x has values of between 0 to 1; p is an integer having the values 1, 2 or 3; and n is an integer having the value of 1, 2, 3 or 4.
- 3. (Original) The compound of claim 2, wherein A is a transition metal or an element of Group IVA of the periodic table, x is 1 and p is 2.
- 4. (Original) The compound of claim 1, having the formula (A_xB_{1-x}) (C_yD_{1-y}) O_n wherein A and B are independently

selected from alkali metals, alkali earth metals, rare earth metals and elements of Group IVA of the periodic table; C and D are independently selected from transition metals and alkali earth metals; x and y have values of between 0 to 1; and n is an integer having the value of 1, 2 or 3.

- 5. (Original) The compound of claim 4, wherein A and B are independently selected from Ba, Sr, Ca, Pb, La, Eu, Li, Na, K and Cs; C and D are independently selected from Ti, Zr, Nb, Ta, Sc, Mg and V; and n is 3.
- 6. (Original) The compound of claim 5, wherein A and B are independently selected from Ba, Sr, Ca, Pb, La and Eu.
- 7. (Original) The compound of claim 5, wherein A and B are independently selected from Li, Na, K and Cs.
- 8. (Original) The compound of claim 5, wherein C and D are independently selected from Ti and Zr.
- 9. (Original) The compound of claim 6, wherein C and D are independently selected from Ti and Zr.

- 10. (Original) The compound of claim 7, wherein C and D are independently selected from Ti and Zr.
- 11. (Original) The compound of claim 5, wherein C and D are independently selected from Nb, Ta, Sc, Mg and V.
- 12. (Original) The compound of claim 6, wherein C and D are independently selected from Nb, Ta and V.
- 13. (Original) The compound of claim 7, wherein C and D are independently selected from Nb, Ta and V.
- 14. (Original) Inorganic, quasi-amorphous compound of claim 4, wherein y=0 and having the formula $(A_xB_{1-x})DO_3$, wherein A, B, D and x are as defined in claim 4.
- 15. (Original) The compound of claim 4 having a pyroelectric coefficient of between about 10^{-12} C/(cm² x K) and about 10^{-7} C/(cm² x K).
- 16. (Original) The compound of claim 14 having a pyroelectric coefficient of between about 10^{-12} C/(cm² x K) and about 10^{-7} C/(cm² x K).

17. (Original) The compound of claim 4 selected from BaTiO₃, CaTiO₃, PbTiO₃, Pb(ZrTi)O₃, Pb(Zr $_{0.35}$ Ti $_{0.65}$)O₃, (PbCa)TiO₃, (PbLa)(ZrTi)O₃, PbLaTiO₃, Pb(ScTa)O₃, Pb(ScNb)O₃, Pb(MgNb)O₃, SrTiO₃, (Sr $_{0.65}$, Ba $_{0.35}$)TiO₃, (Ba $_{0.70}$, Sr $_{0.30}$)TiO₃ and EuTiO₃.

- 18. (Original) The compound of claim 17 having a pyroelectric coefficient of between about 10^{-12} C/(cm² x K) and about 10^{-7} C/(cm² x K).
- 19. (Original) The compound of claim 17 being selected from BaTiO₃, PbTiO₃ and SrTiO₃.
 - 20. (Original) The compound of claim 18 being BaTiO3.
- 21. (Currently Amended) A process for preparing pyroelectric compound, comprising applying a mechanical strain to a substantially amorphous compound of the formula $(A_xB_{1-}x)(C_yD_{1-y})O_n$ as defined in claim 4wherein A and B are independently selected from alkali metals, alkali earth metals, rare earth metals and elements of Group IVA of the periodic table; C and D are independently selected from transition metals and alkali earth metals; x and y have values of between 0 to 1; and n is an integer having the value of 1, 2 or 3, said mechanical strain being controlled so as to prevent

crystallization of said compound, thereby obtaining inorganic quasi-amorphous compound having pyroelectric properties.

- 22. (Original) The process of claim 21, wherein said mechanical strain is obtained by a temperature gradient.
- 23. (Currently Amended) The process of claim 21, wherein said amorphous compound has the formula $(A_xB_{1-x})DO_{3.7}$ wherein A, B, D and x have the meanings as defined in claim 14.
- 24. (Currently Amended) Inorganic quasi-amorphous compound of the formula (A_xB_{1-x}) (C_yD_{1-y}) O_3 as defined in claim 14 wherein A and B are independently selected from alkali metals, alkali earth metals, rare earth metals and elements of Group IVA of the periodic table; C and D are independently selected from transition metals and alkali earth metals; and x and y have values of between 0 to 1, preparable by the process of claim 21.
- 25. (Original) A device comprising the compound according to claim 1 in the form of a film coating on a substrate.

26. (Original) A device comprising the compound according to claim 4 in the form of a film coating on a substrate.

- 27. (Original) The device of claim 26, wherein the substrate is selected from Si, SiO_2 and glass.
- 28. (Original) The device of claim 27, wherein the thickness of the coating layer is below 0.5 micron.
- 29. (Original) A device comprising the compound of claim 1, the device being operable as a sensor for sensing an external field including at least one of the following: temperature field, magnetic filed and electric field.
- 30. (Original) A device comprising the compound of claim 4, the device being operable as a sensor for sensing an external field including at least one of the following: temperature field, magnetic filed and electric field.
- 31. (Original) A device having an acoustic wave propagation element including the compound of claim 1.

- 32. (Original) A device having an acoustic wave propagation element including the compound of claim 4.
- 33. (Original) A device having an acoustic wave propagation element including the compound of claim 5.
- 34. (Original) A birefringent medium comprising the compound of claim 1.
- 35. (Original) A birefringent medium comprising the compound of claim 4.
- 36. (Original) A device comprising the compound according to claim 1.
- 37. (Original) A device comprising the compound according to claim 4.
- 38. (Original) A device comprising a compound according to claim 3 in the form of a film coating on a substrate.
- 39. (Original) The device of claim 38, wherein the substrate is selected from Si, SiO_2 and glass.

40. (Original) The device of claim 39, wherein the compound is SiO_2 .